

FAST SWITCHING THYRISTOR

ATF624

New design for induction heating power converters

Repetitive voltage up to

1400 V

Mean forward current

1526 A

Surge current

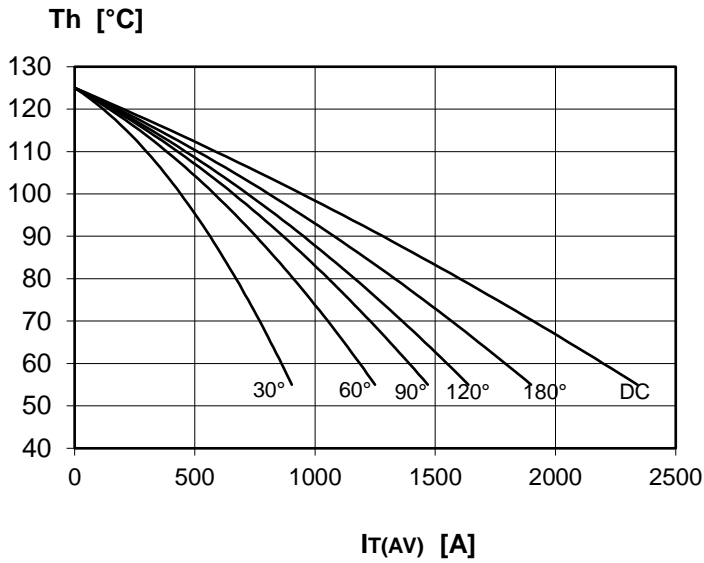
15 kA

TARGET SPECIFICATION

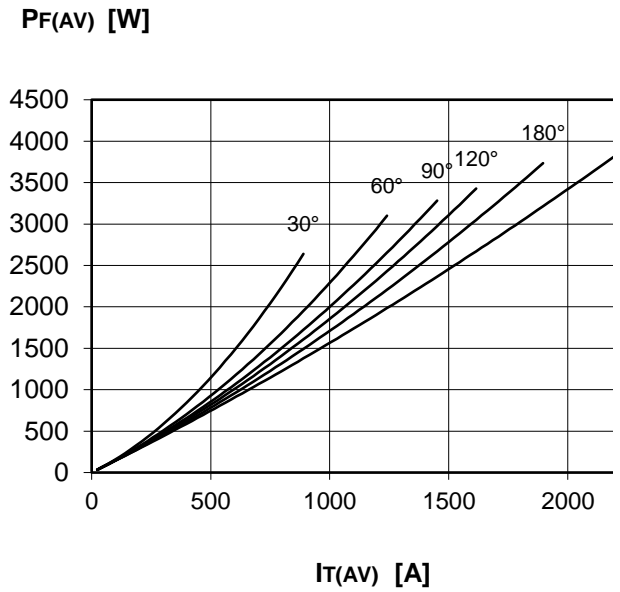
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| Symbol | Characteristic | Conditions | T _j [°C] | Value |
|--|--|---|---------------------|------------------------|
| BLOCKING | | | | |
| V _{RRM} | Repetitive peak reverse voltage | | 125 | 1400 |
| V _{RSM} | Non-repetitive peak reverse voltage | | 125 | 1500 |
| V _{DRM} | Repetitive peak off-state voltage | | 125 | 1400 |
| I _{RRM} | Repetitive peak reverse current | V=VRRM | 125 | 100 |
| I _{DRM} | Repetitive peak off-state current | V=VDRM | 125 | 100 |
| CONDUCTING | | | | |
| I _{T(AV)} | Mean forward current | 180° sin ,50 Hz, Th=55°C, double side cooled | | 1946 |
| I _{T(AV)} | Mean forward current | 180° sin ,50 Hz, Tc=80°C, double side cooled | | 1526 |
| I _{TSM} | Surge forward current | Sine wave, 10 ms | 125 | 15 |
| I ² t | I ² t | without reverse voltage | | 1125 x 10 ³ |
| V _T | On-state voltage | On-state current = 2000 A | 25 | 2,00 |
| V _{T(TO)} | Threshold voltage | | 125 | 1,42 |
| r _T | On-state slope resistance | | 125 | 0,145 |
| SWITCHING | | | | |
| di/dt | Critical rate of rise of on-state current, min. | From 75% VDRM to 1200A | 125 | 800 |
| dv/dt | Critical rate of rise of off-state voltage, min. | Linear ramp up to VDRM= 1400 V, Gate Open | 125 | 600 |
| t _d | Gate controlled delay time, typical | VD=67% VDRM; IT=1500A; diT/dt=60 A/μs IFG=2 A, tr ≤ 0,5 μs | 25 | 1,5 |
| t _q | Circuit commutated turn-off time, typical | dv/dt = 200 V/μs VD=1050 V di/dt = -25 A/μs, IT= 1000 A VR=50 V | 125 | 25 |
| Q _{rr} | Reverse recovery charge | di/dt = -60A/μs, IT= 1000 A | 125 | 650 |
| I _{rr} | Peak reverse recovery current | VR=100 V | | 200 |
| I _H | Holding current, typical | gate open circuit | 25 | 250 |
| I _L | Latching current, typical | | 25 | |
| GATE | | | | |
| V _{GT} | Gate trigger voltage | VD=5 V | 25 | 3,00 |
| I _{GT} | Gate trigger current | VD=5 V | 25 | 300 |
| V _{GD} | Non-trigger gate voltage, min. | VD=VDRM | 125 | 0,25 |
| V _{FGM} | Peak gate voltage (forward) | | | 30 |
| I _{FGM} | Peak gate current | | | 10 |
| V _{RGM} | Peak gate voltage (reverse) | | | 5 |
| P _{GM} | Peak gate power dissipation | Pulse width 100 μs | | 30 |
| P _G | Average gate power dissipation | | | 4 |
| MOUNTING | | | | |
| R _{th(j-h)} | Thermal impedance, DC | Junction to heatsink, double side cooled | | 17 |
| R _{th(c-h)} | Thermal impedance | Case to heatsink, double side cooled | | 2 |
| T _j | Operating junction temperature | | | -30 / 125 |
| F | Mounting force | | | 17.0 / 21.0 |
| | Mass | | | 520 |
| ORDERING INFORMATION : ATF624 S 14S | | | | |
| standard specification | | | | tq code |
| VRRM/100 | | | | |
| D 10 μs | C 12 μs | B 15 μs | A 20 μs | |
| M 30 μs | N 35 μs | P 40 μs | R 45 μs | |
| T 60 μs | U 70 μs | W 80 μs | X 100 μs | |

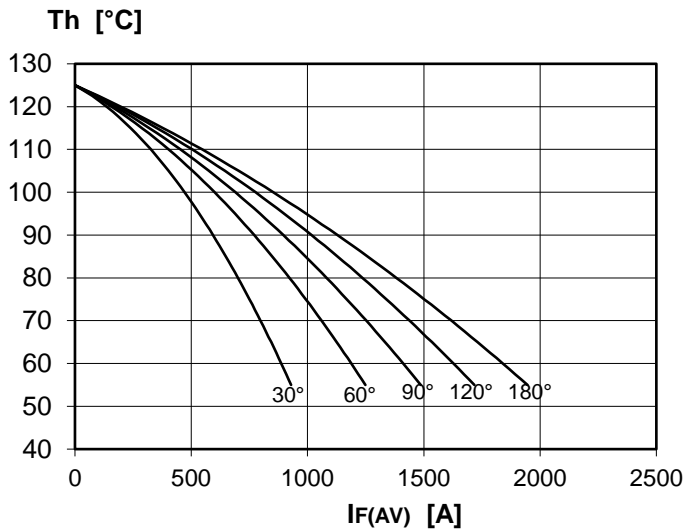
Dissipation characteristics



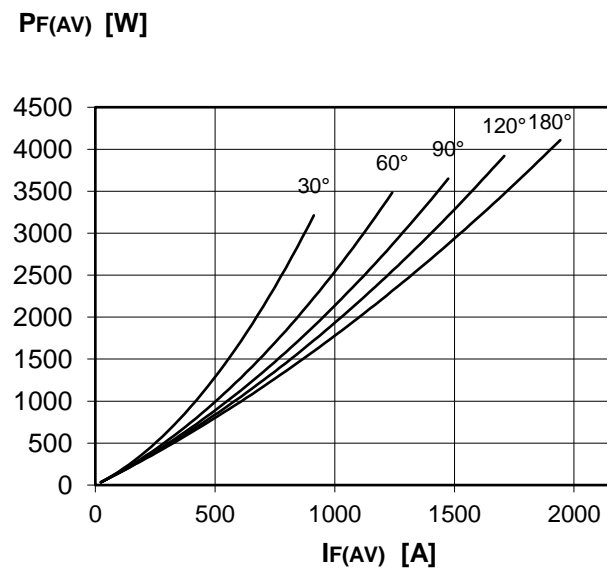
Max permissible heatsink temperature vs. mean on state current (square wave; 50 Hz)



On state power losses vs. mean on state current (square wave; 50 Hz)



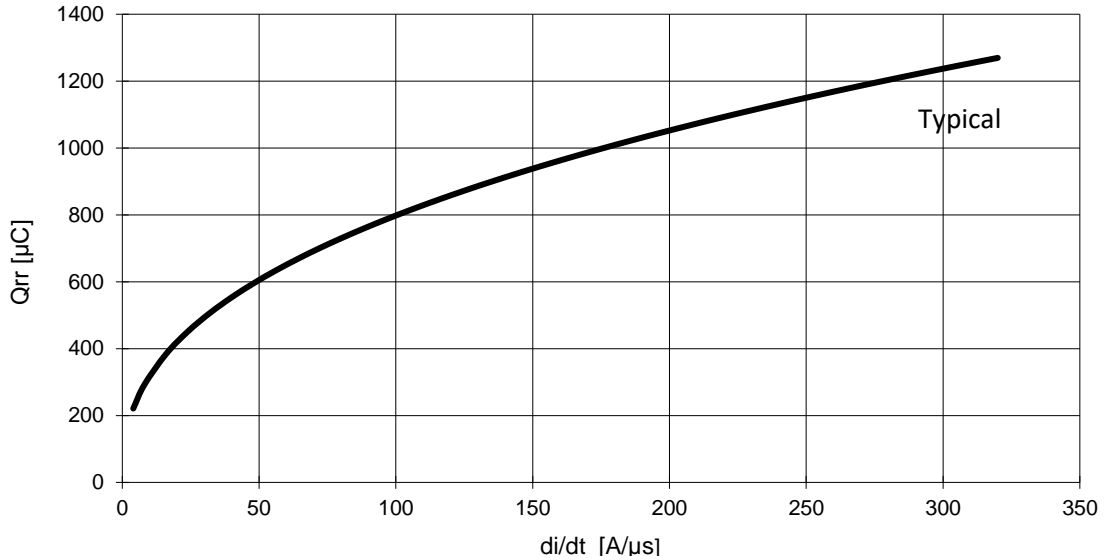
Max permissible heatsink temperature vs. mean on state current (sine wave; 50 Hz)



On state power losses vs. mean on state current (sine wave; 50 Hz)

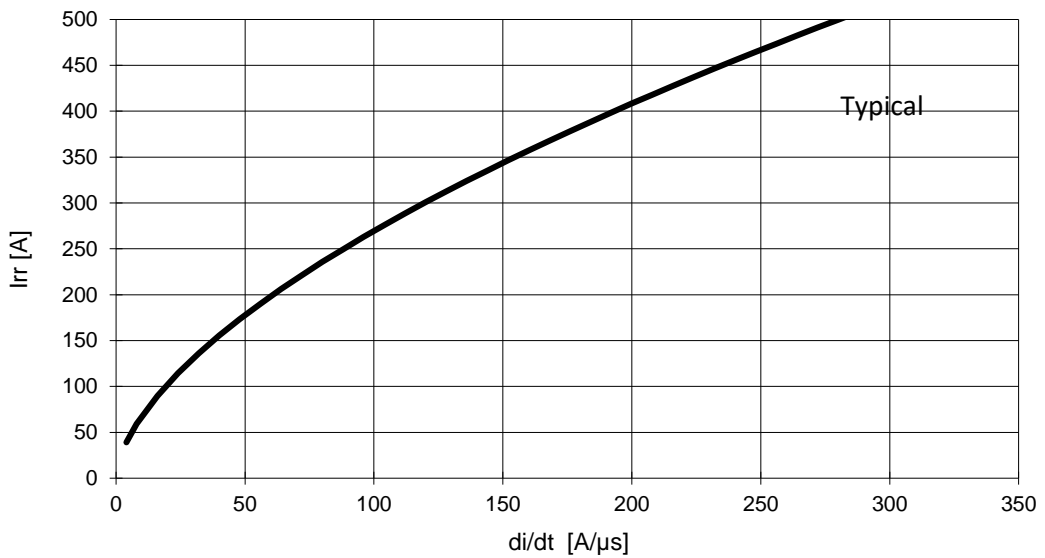
REVERSE RECOVERY CHARGE

@ $T_j = 125\text{ }^\circ\text{C}$
 $I_T = 1000\text{ A}$



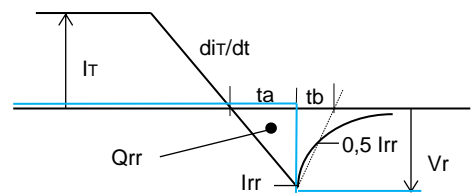
REVERSE RECOVERY CURRENT

@ $T_j = 125\text{ }^\circ\text{C}$
 $I_T = 1000\text{ A}$



$$t_a = I_{rr} / (di_T/dt) \quad t_b = t_{rr} - t_a$$

Energy dissipation during recovery $E_{off} = V_r \cdot (Q_{rr} - I_{rr} \cdot t_a / 2)$

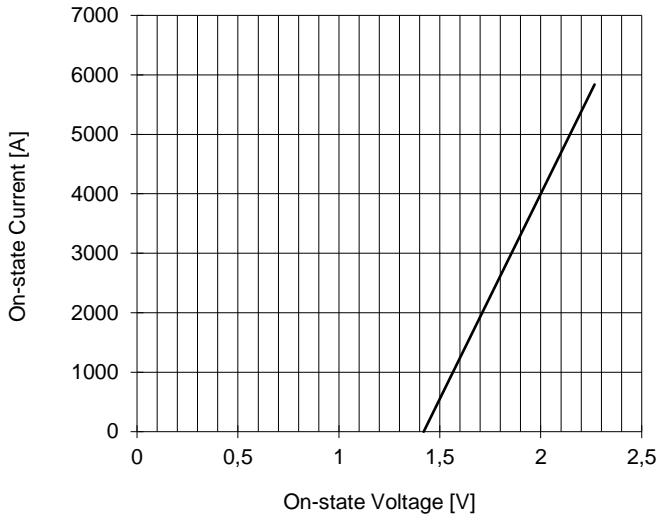


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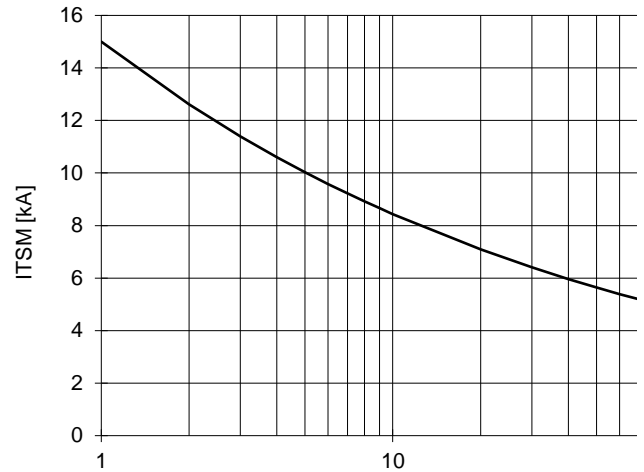


TARGET SPECIFICATION Aug. 18 - Issue: 2

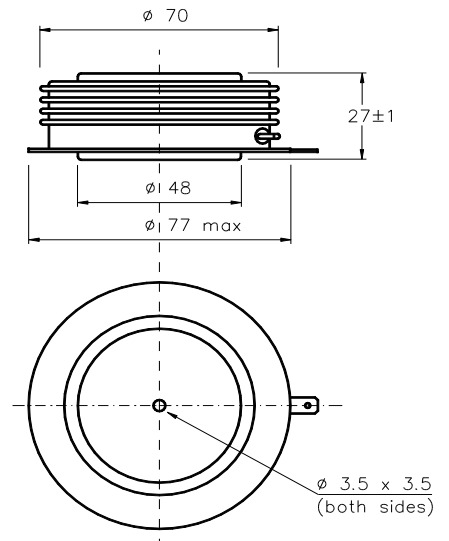
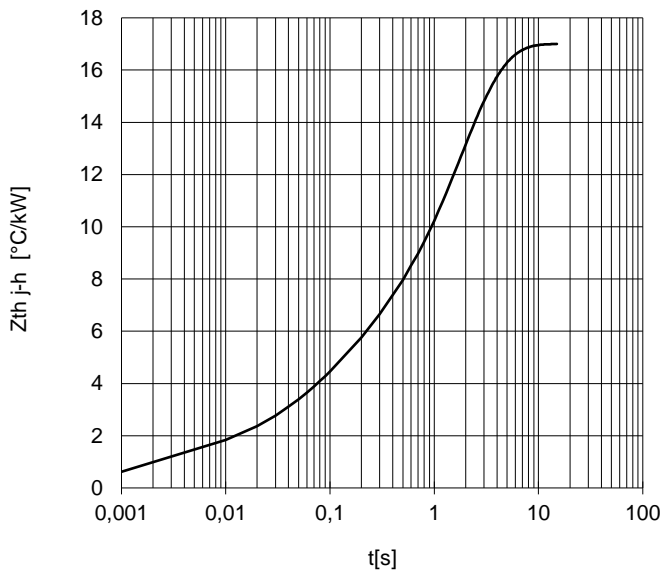
ON-STATE CHARACTERISTIC
T_j = 125 °C



SURGE CHARACTERISTIC
T_j = 125 °C



TRANSIENT THERMAL IMPEDANCE
DOUBLE SIDE COOLED



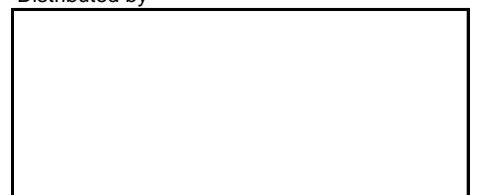
Dimensions
in mm



Cathode terminal type DIN 46244 - A 4.8 - 0.8

Gate terminal type AMP 60598 - 1

Distributed by



All the characteristics given in this data sheet are guaranteed only with uniform clamping force, cleaned and lubricated heatsink, surfaces with flatness < .03 mm and roughness < 2 μm.
In the interest of product improvement POSEICO SpA reserves the right to change any data given in this data sheet at any time without previous notice.
If not stated otherwise the maximum value of ratings (symbols over shaded background) and characteristics is reported.

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| Unit |
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| V |
| V |
| V |
| mA |
| mA |

| |
|------------------|
| A |
| A |
| kA |
| A ² s |
| V |
| V |
| mohm |

| |
|------|
| A/μs |
| V/μs |
| μs |
| μs |

| |
|----|
| μC |
| A |
| mA |
| mA |

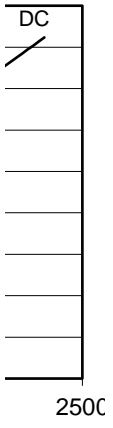
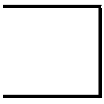
| |
|----|
| V |
| mA |
| V |
| V |
| A |
| V |
| W |
| W |

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|-------|
| °C/kW |
| °C/kW |
| °C |
| kN |
| g |

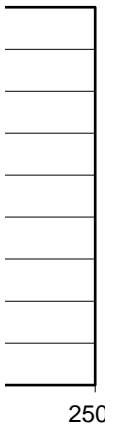
| |
|---------|
| L 25 μs |
|---------|

| |
|---------|
| S 50 μs |
|---------|

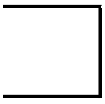
| |
|----------|
| Y 150 μs |
|----------|

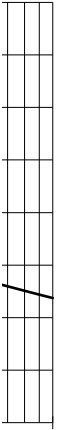
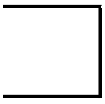


t (square



(sine





100

